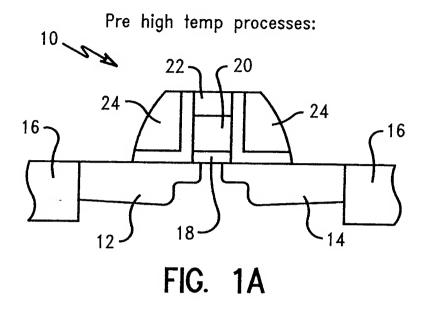
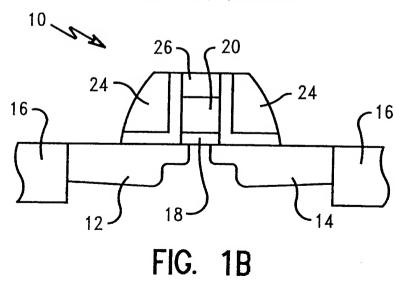
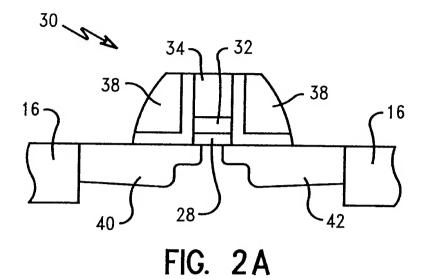
## FIS920020157US1 Ricky S. Amos et al TLT 1/16



## Post high temp processes:





Pre high temp processes:

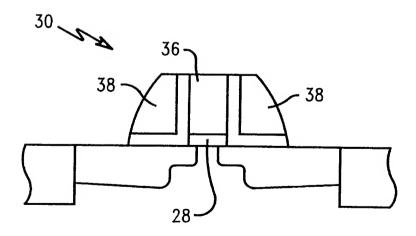
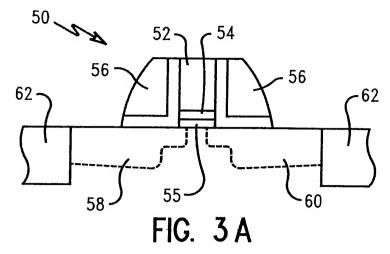
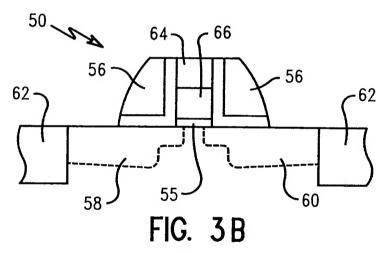


FIG. 2B
Post high temp processes:

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Pre high temp processes:



Post high temp processes:

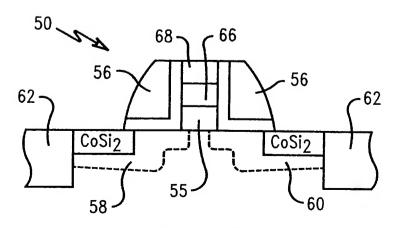
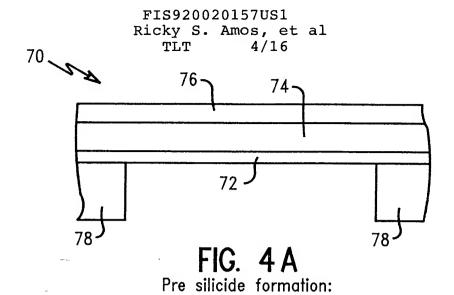
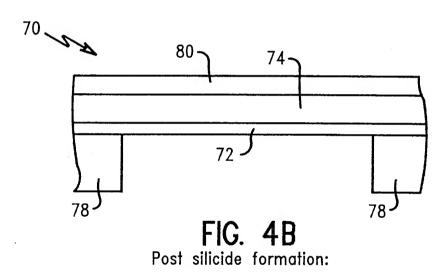


FIG. 3C

Post source/drain/gate silicide (assumed CoSi2)





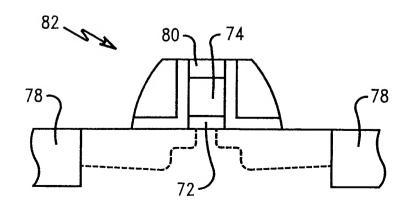
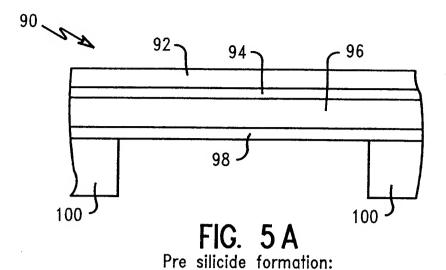


FIG. 4C
Post high temp processes:



Silicide 1 Silicide 2

98

FIG. 5B

Post silicide formation:

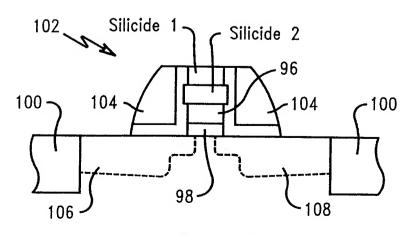
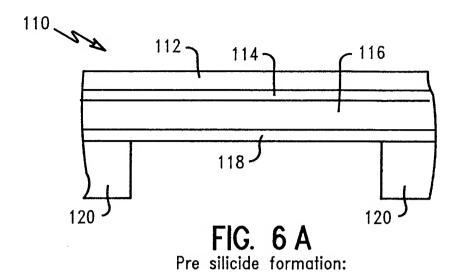
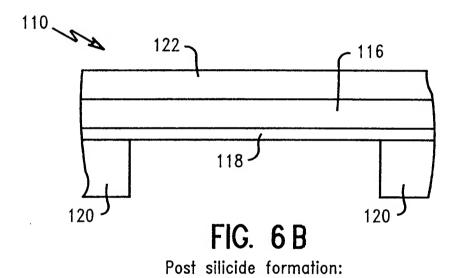


FIG. 5 C
Post high temp processes:





120 124 120

FIG. 6 C
Post high temp processes:

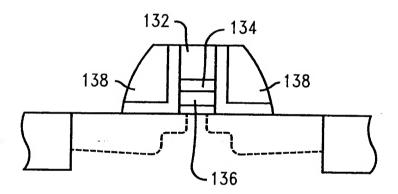
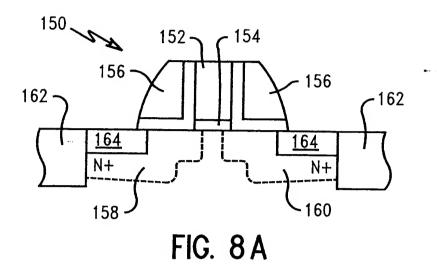


FIG. 7



166 174 168 170 172 164 164 160 162

FIG. 8B

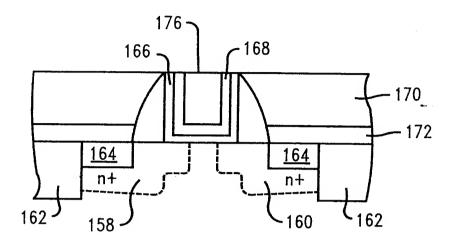


FIG. 8C

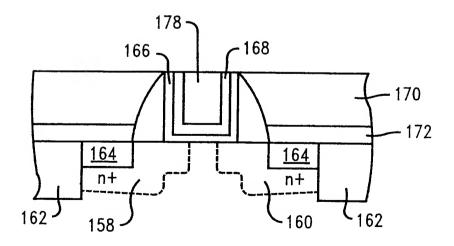
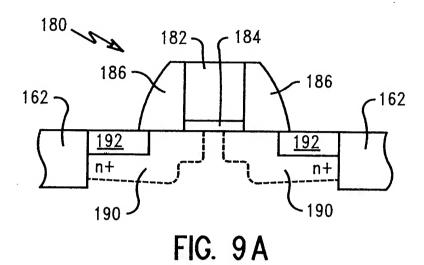


FIG. 8D



202 198 204 200 194 196 196 190 190

FIG. 9B

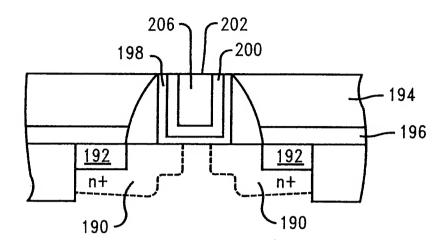


FIG. 9 C

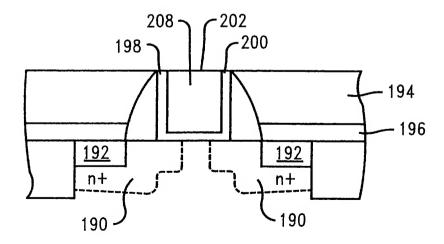
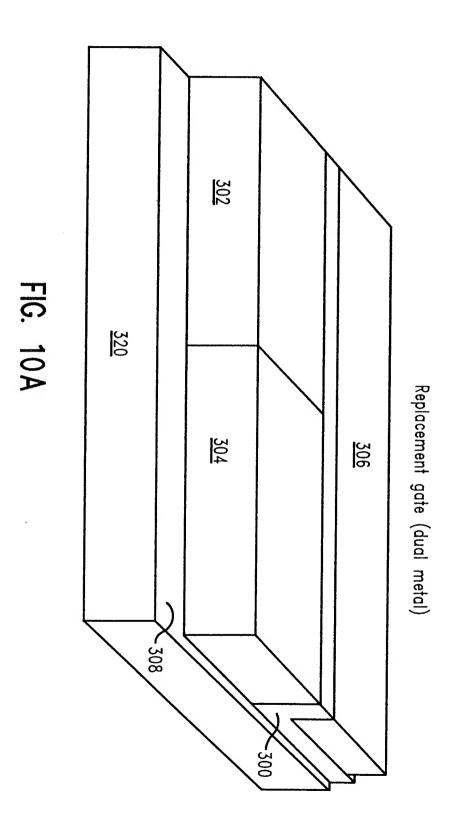
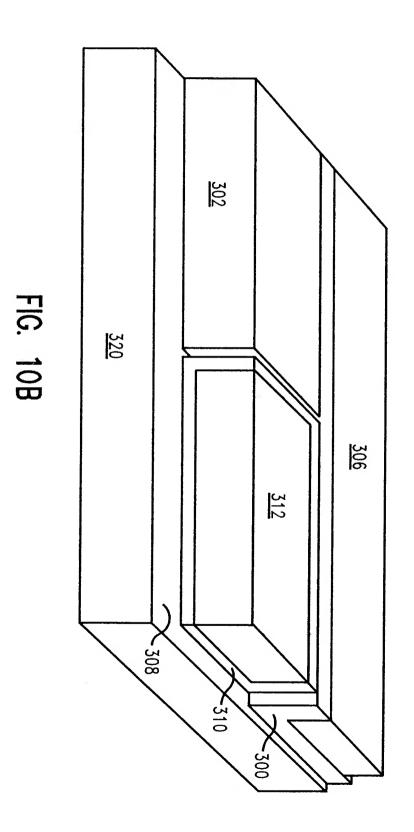
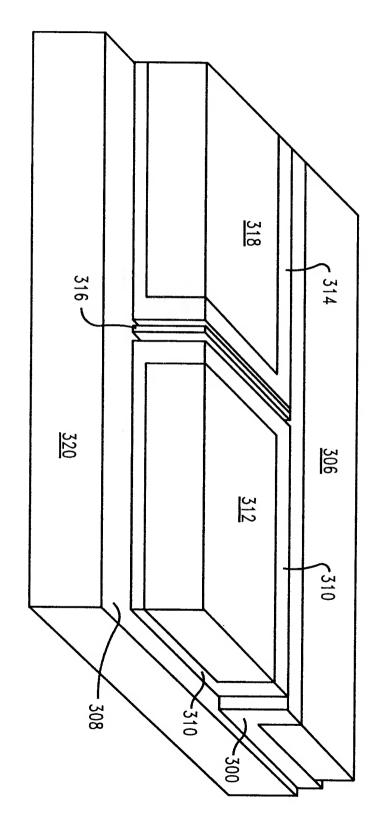


FIG. 9D



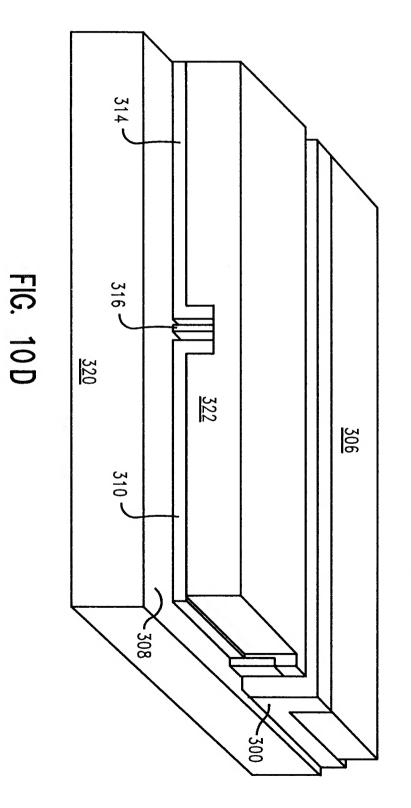


Replacement gate (dual metal)
-> Undoped Poly-Si deposition + CMP



Replacement gate (dual metal)
-> Undoped Poly deposition + CMP

FIG. 10C



Replacement gate (dual metal)
-> Poly- Si RIE back / CMP

Replacement gate (dual metal) -> Co-silicidation

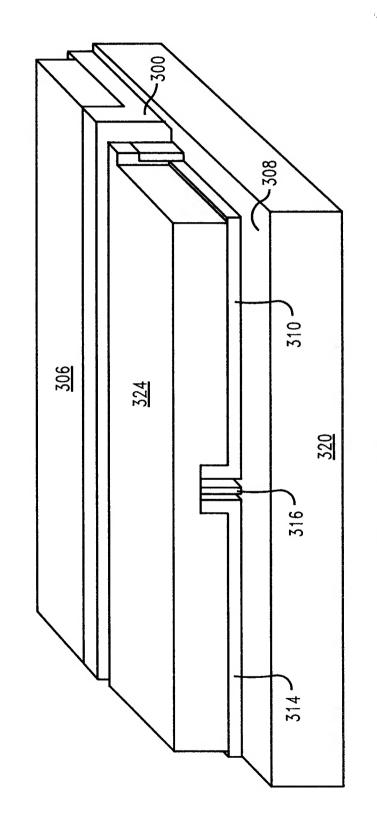


FIG. 10 E